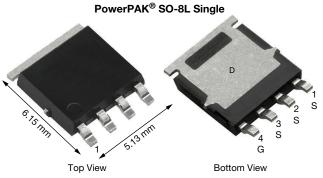


Vishay Siliconix

Automotive N-Channel 75 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	75
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.026
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.032
I _D (A)	30
Configuration	Single



FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_g and UIS tested
- Material categorization: For definitions of compliance please see <u>www.vishav.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE

Top View	Bottom View	N-Channel MOSFET
ORDERING INFORMATION		
Package		PowerPAK SO-8L
Lead (Pb)-free and Halogen-free		SQJ486EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS	S (T _C = 25 °C, unles	s otherwise noted	ł)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	75	V	
Gate-Source Voltage		V _{GS}	± 20		
Constinueron Dunin Comment 3	T _C = 25 °C		30		
Continuous Drain Current ^a	T _C = 125 °C	I _D	17		
Continuous Source Current (Diode Conduction	on) ^a	I _S	50	А	
Pulsed Drain Current ^b		I _{DM}	120		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	13		
L = Single Pulse Avalanche Energy		E _{AS}	9	mJ	
	T _C = 25 °C	PD	56	W	
Maximum Power Dissipation ^b	T _C = 125 °C	FD	19	vv	
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak Tempera	ture) ^{e, f}		260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	70	°C/W
Junction-to-Case (Drain)		R _{thJC}	2.7	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.

S14-1445-Rev. B, 14-Jul-14

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Vishay Siliconix

SQJ486EP

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	75	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.1	1.6	2.1	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 75 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	$V_{DS} = 75 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 75 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	А
		V _{GS} = 10 V	I _D = 5.9 A	-	0.022	0.026	
	Р	V _{GS} = 10 V	I _D = 5.9 A, T _J = 125 °C	-	-	0.043	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 5.9 A, T _J = 175 °C	-	-	0.056	
		$V_{GS} = 4.5 V$	I _D = 5.3 A	-	0.026	0.032	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 5.9 A		-	75	-	S
Dynamic ^b				•			
Input Capacitance	C _{iss}			-	1109	1386	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 37 V, f = 1 MHz	-	146	183	pF
Reverse Transfer Capacitance	C _{rss}			-	63	79	
Total Gate Charge ^c	Qg			-	22	34	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 37 \text{ V}, \text{ I}_{D} = 8 \text{ A}$	-	2.7	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	5	-	1
Gate Resistance	R _g	f = 1 MHz		0.45	0.9	1.5	Ω
Turn-On Delay Time ^c	t _{d(on)}				9	13	- ns
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 37 \ V, \ R_L = 30 \ \Omega \\ I_D \cong 1 \ A, \ V_{GEN} = 10 \ V, \ R_g = 1 \ \Omega \end{array}$		-	11	17	
Turn-Off Delay Time ^c	t _{d(off)}			-	21	31	
Fall Time ^c	t _f			-	14	21	
Source-Drain Diode Ratings and Chara	acteristics ^b	• 					
Pulsed Current ^a	I _{SM}			-	-	120	Α
	V _{SD}	1	= 3.9 A, V _{GS} = 0		0.76	1.2	v

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

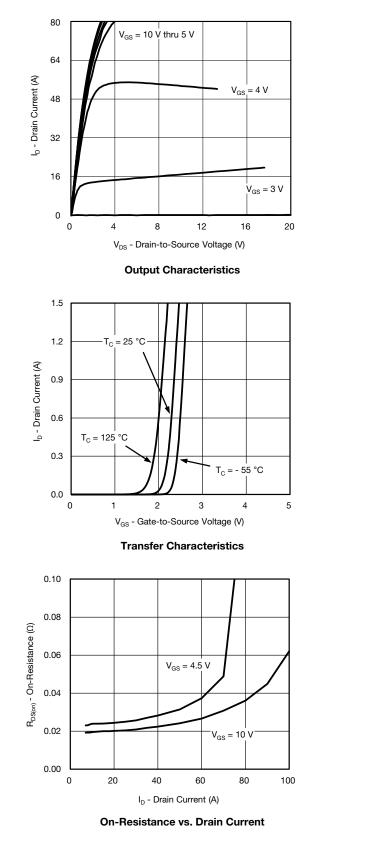
c. Independent of operating temperature.

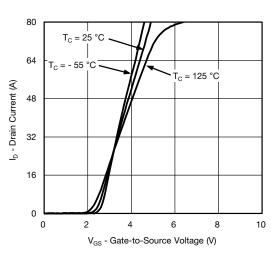
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

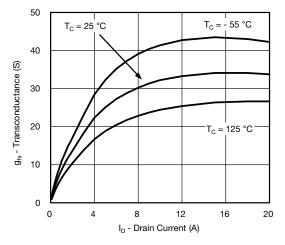


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

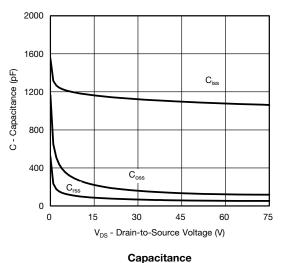




Transfer Characteristics



Transconductance



S14-1445-Rev. B, 14-Jul-14

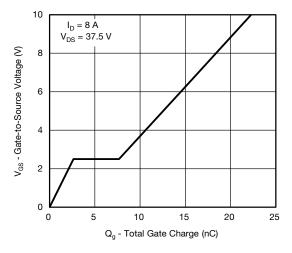
Document Number: 62902

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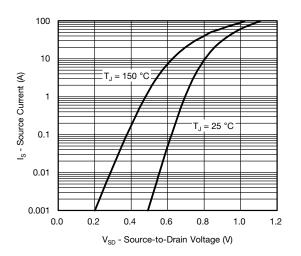


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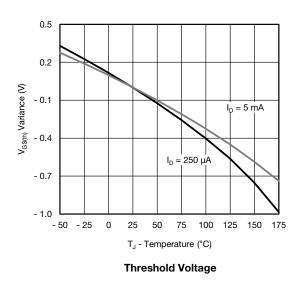
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

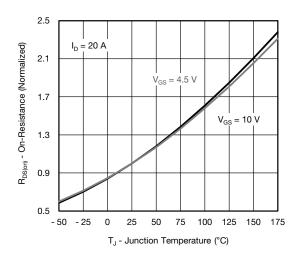


Gate Charge

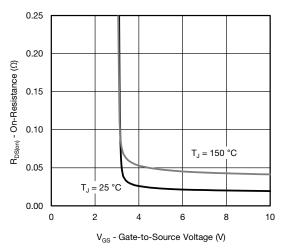


Source Drain Diode Forward Voltage

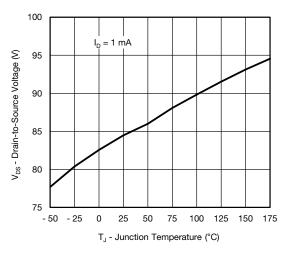




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

S14-1445-Rev. B, 14-Jul-14

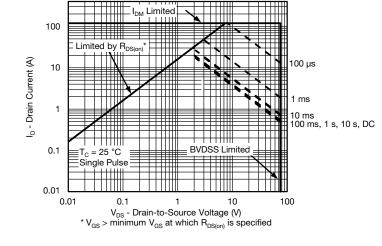
4

Document Number: 62902

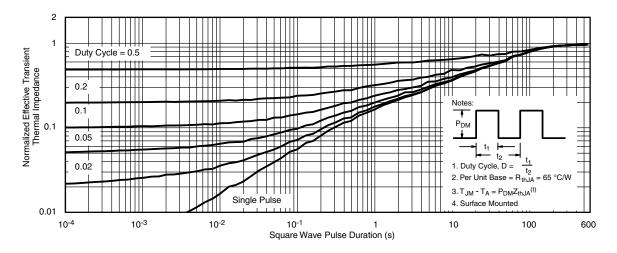
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

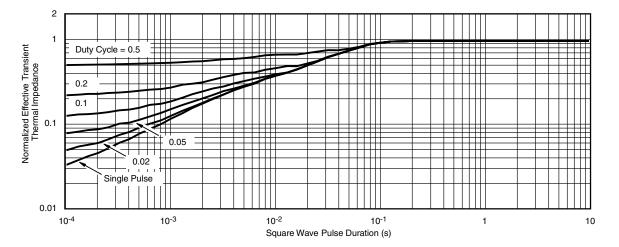


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62902.



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REVISION HISTORY^a

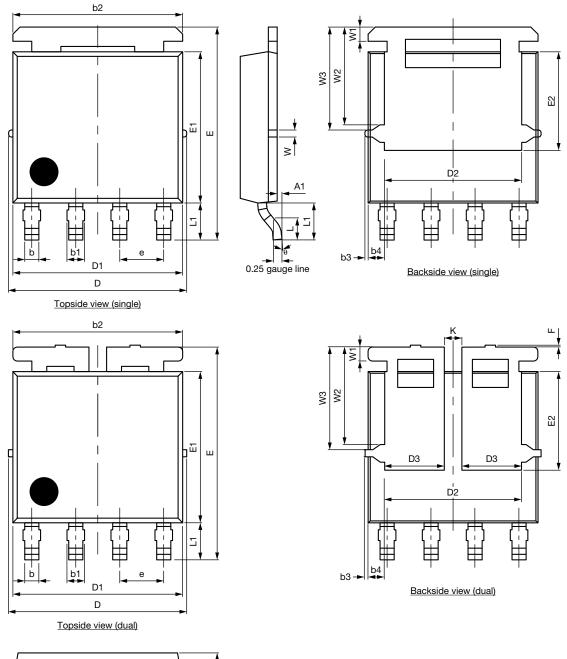
REVISION	DATE	DESCRIPTION OF CHANGE
В	08-Jul-14	Pin 2 in pin-out diagram corrected to S for source

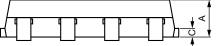
Note

a. As of April 2014









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Package Information



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DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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